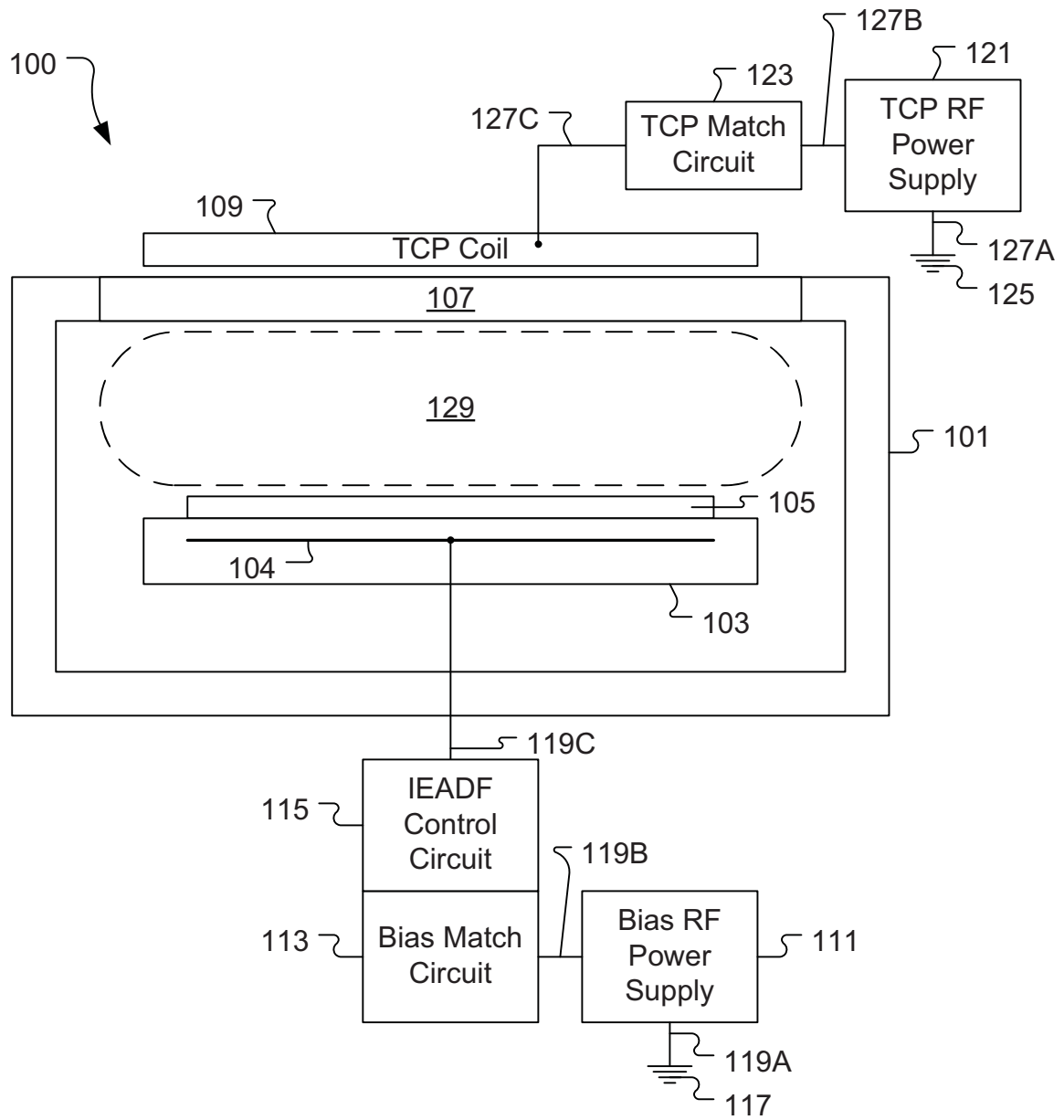
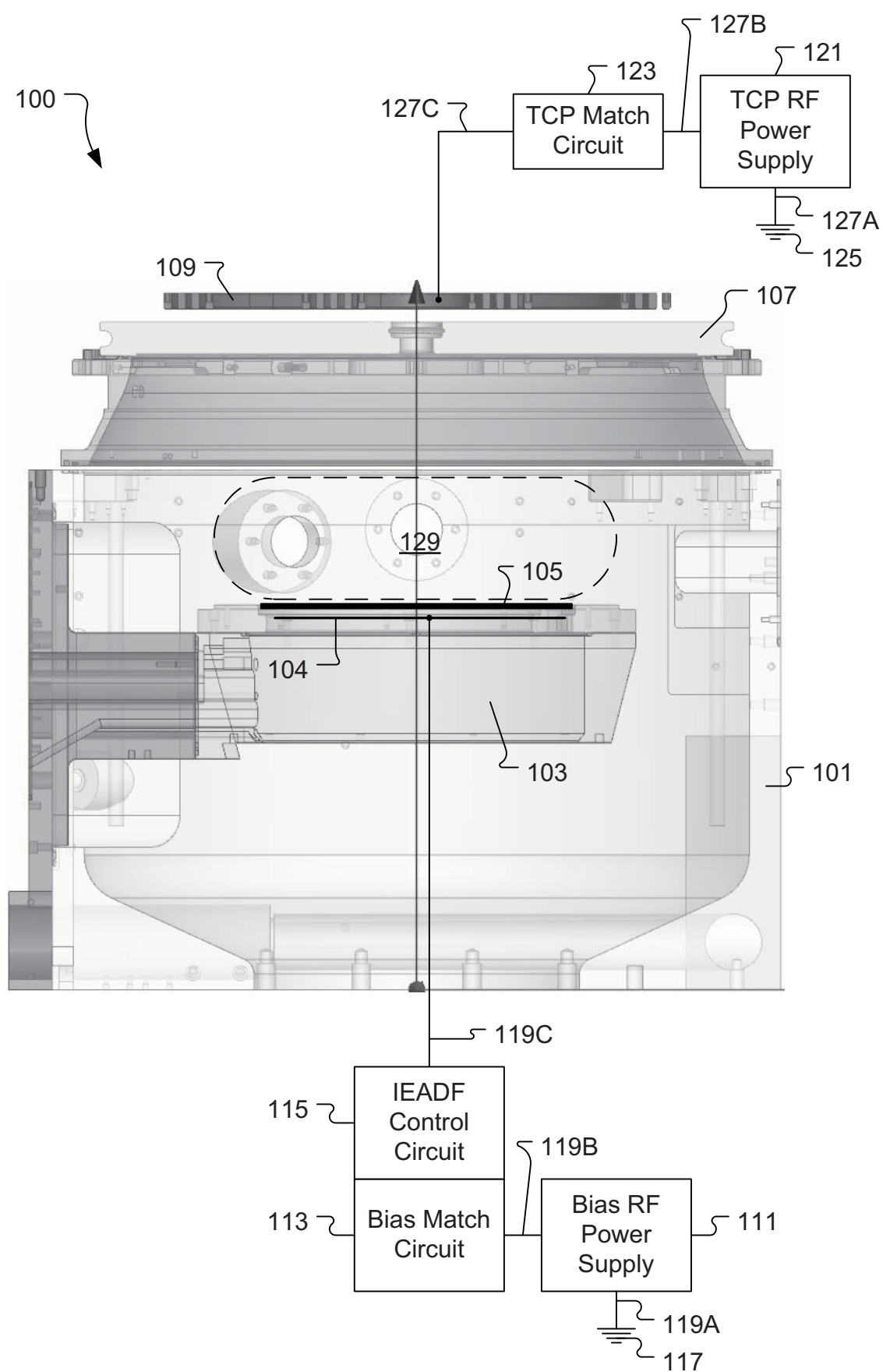


**FIG. 1A**

**FIG. 1B**

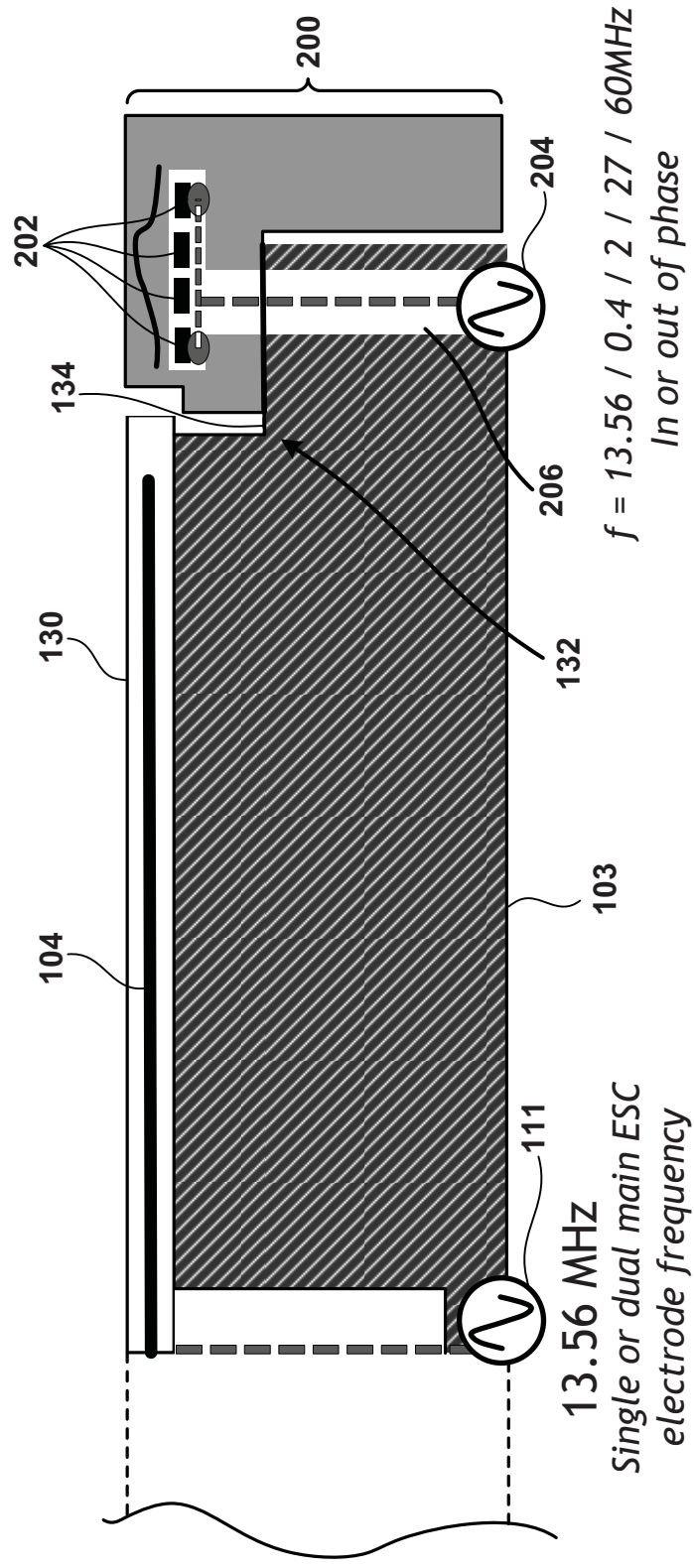


FIG. 2A

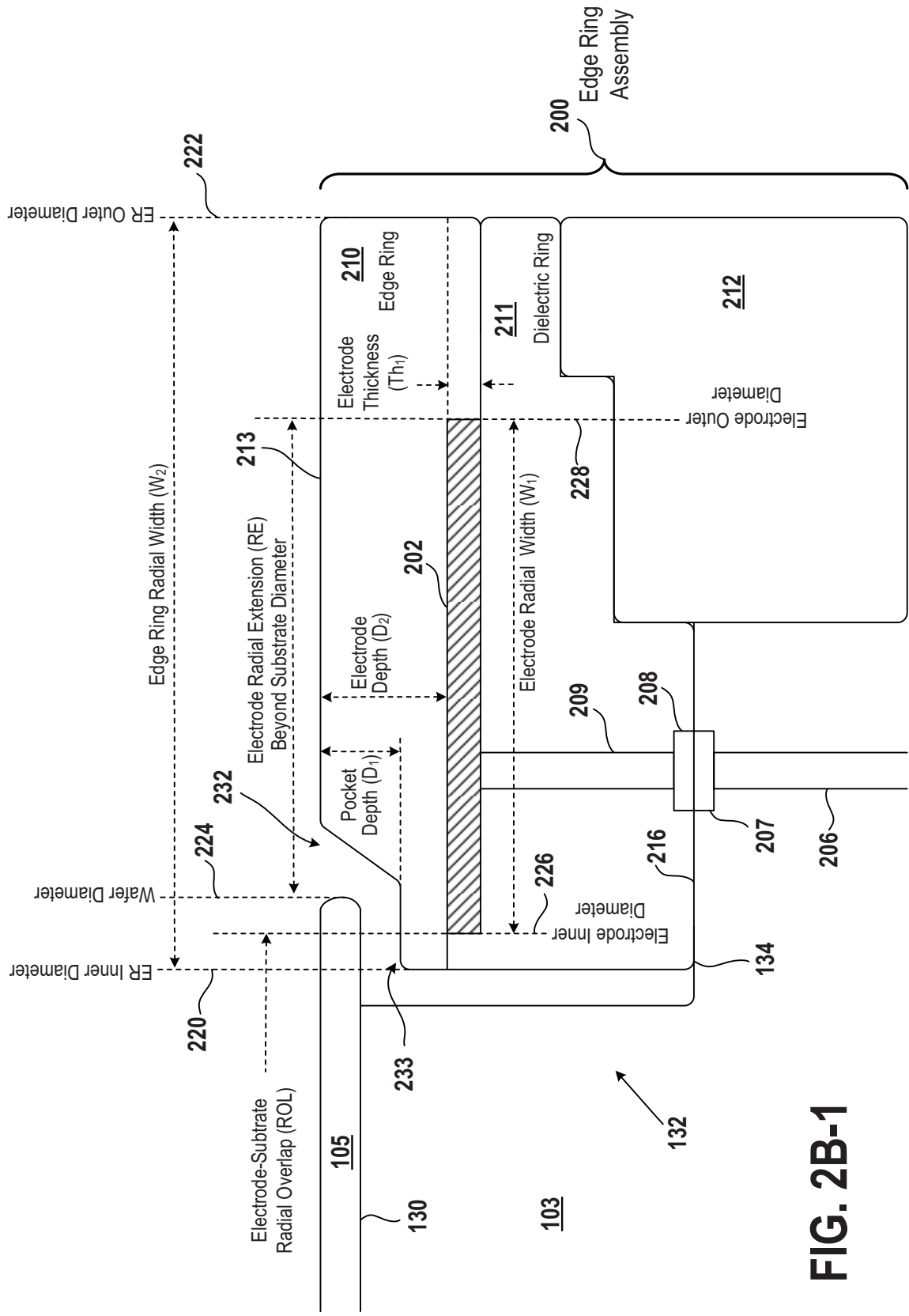


FIG. 2B-1

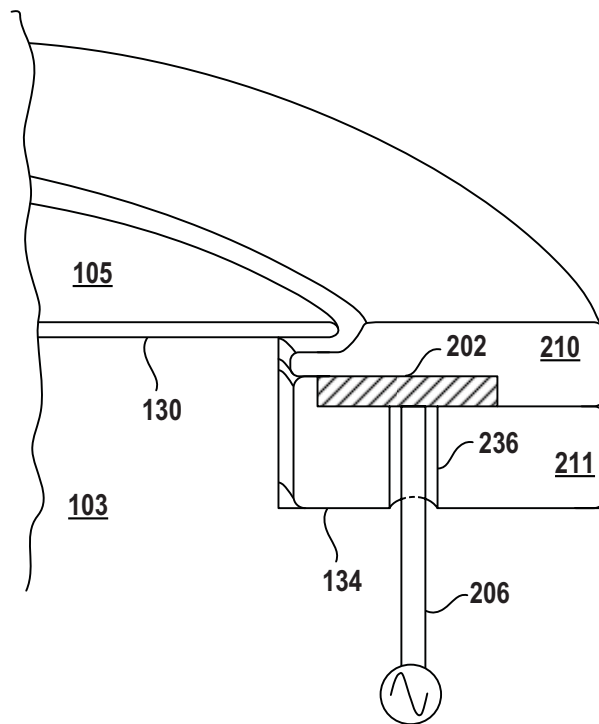
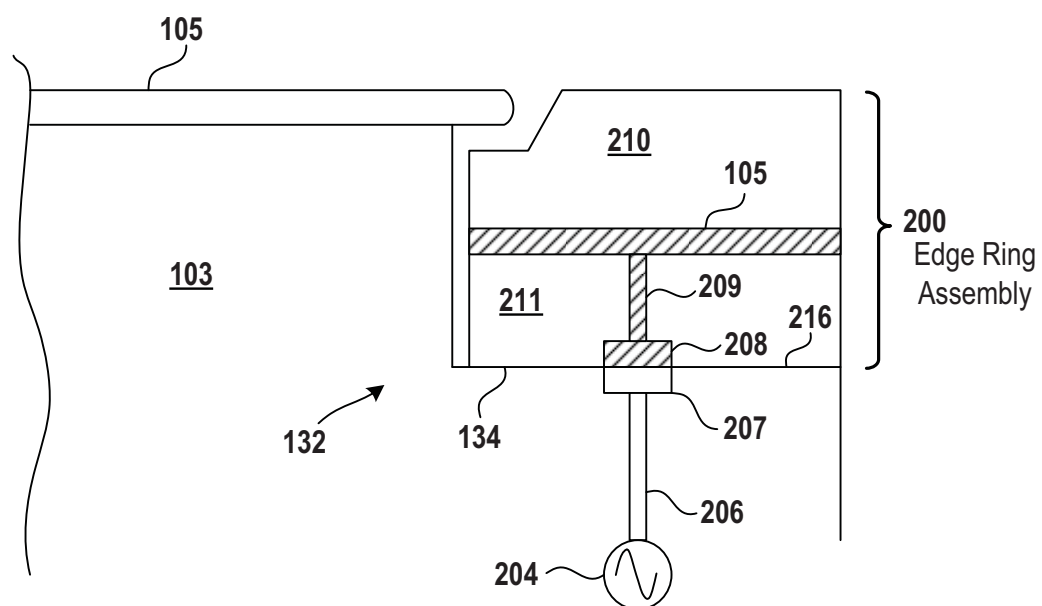
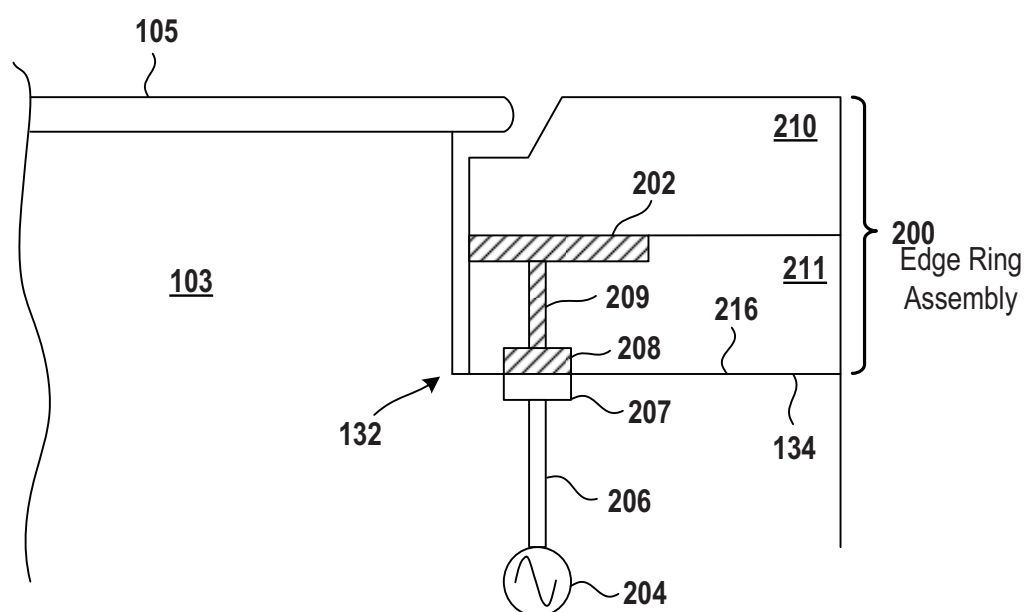
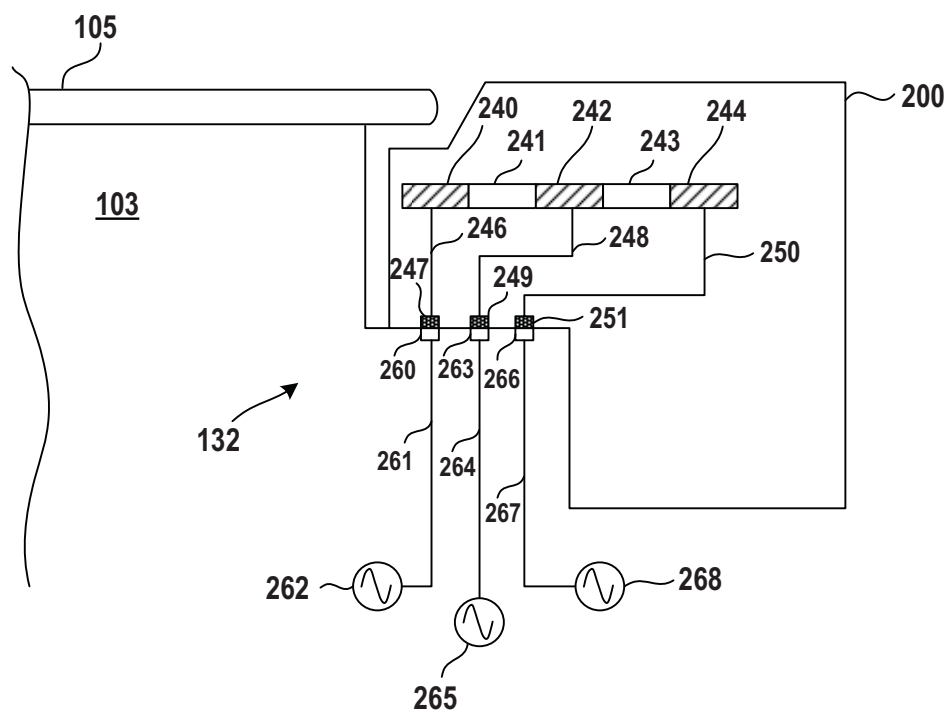
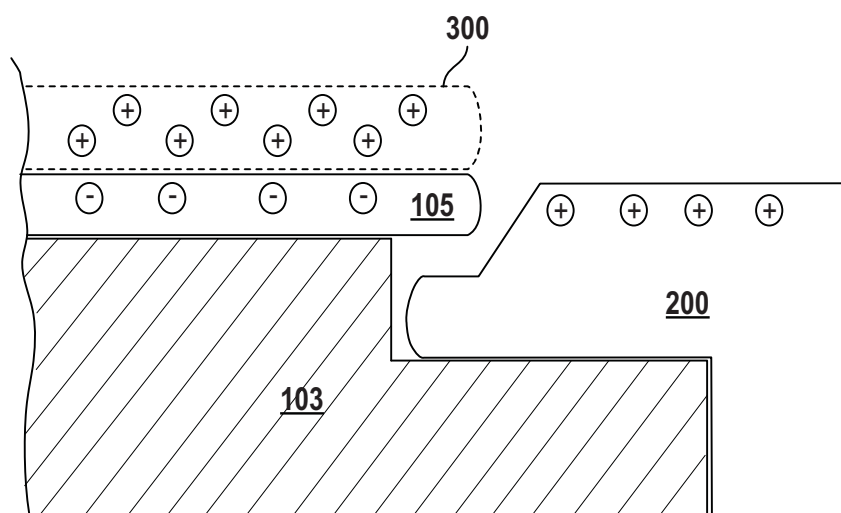
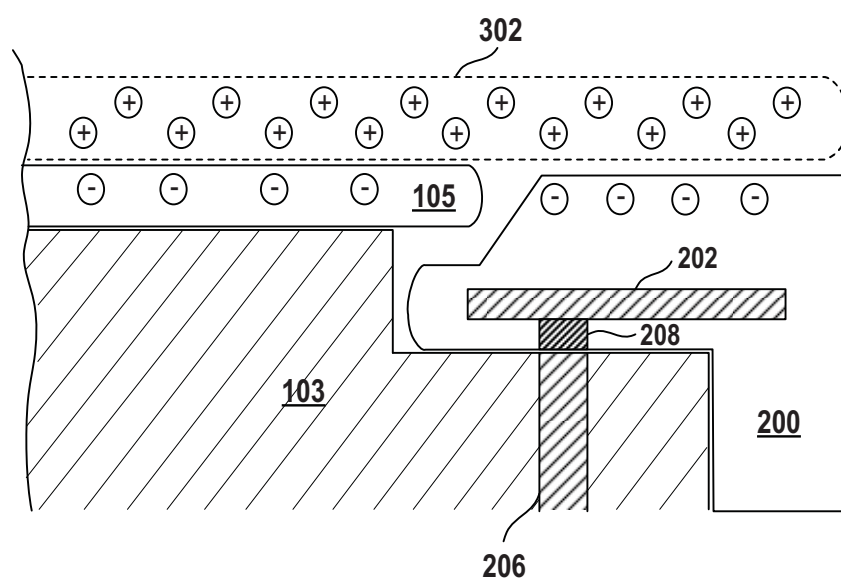


FIG. 2B-2

**FIG. 2C****FIG. 2D**

**FIG. 2E**

**FIG. 3A****FIG. 3B**

2MHz Powered Edge Ring Reduces Ion Focusing at Extreme Wafer Edge and
Provides Way to Control Ion Trajectories

10mT/900W TCP / 200Ar / 200V_{b,main} (10MHz) / ERE (2MHz) X V_b

X V_b = 0Vb

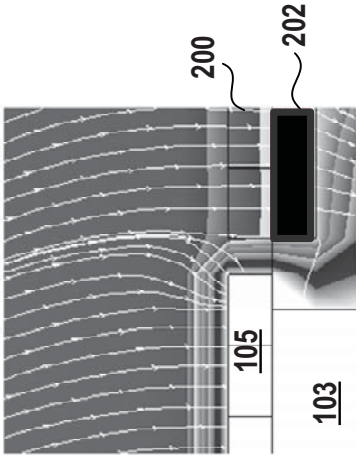


FIG. 4A

X V_b = 100Vb

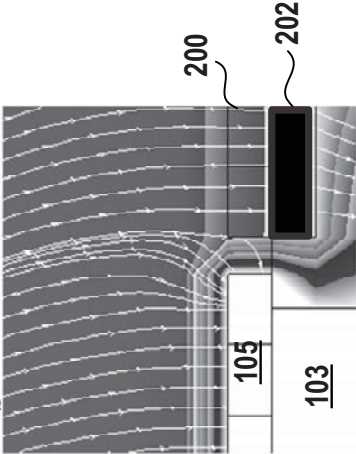


FIG. 4B

X V_b = 300Vb

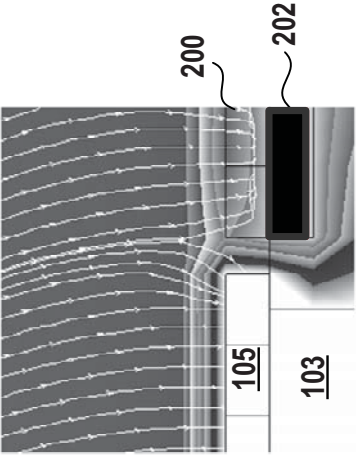


FIG. 4C

500Vb

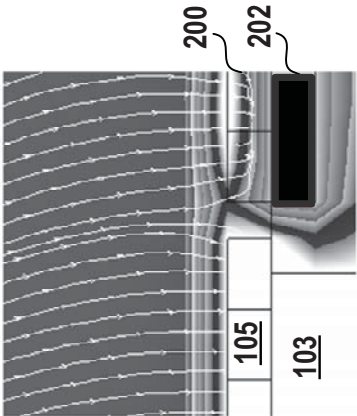


FIG. 4D

700Vb

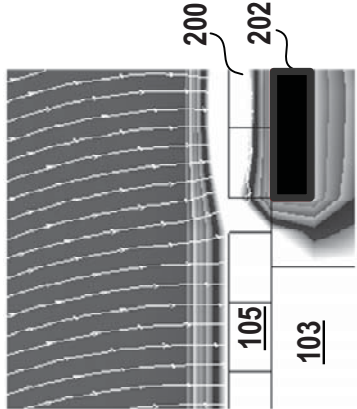


FIG. 4E



Buried Electrode
2MHz RF



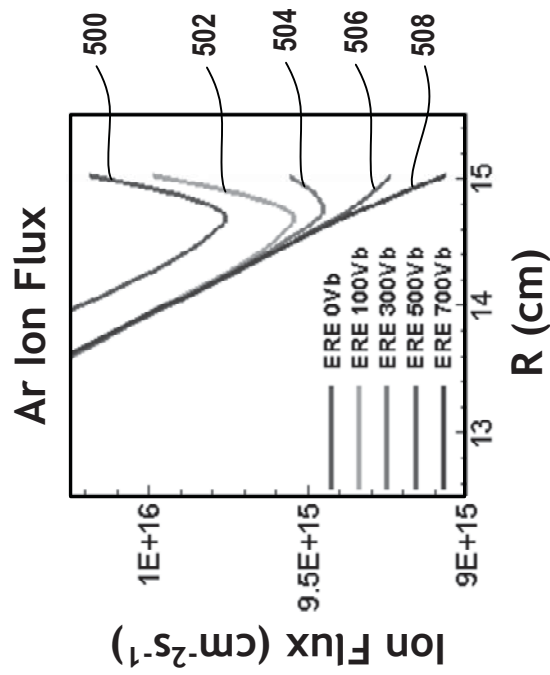


FIG . 5B

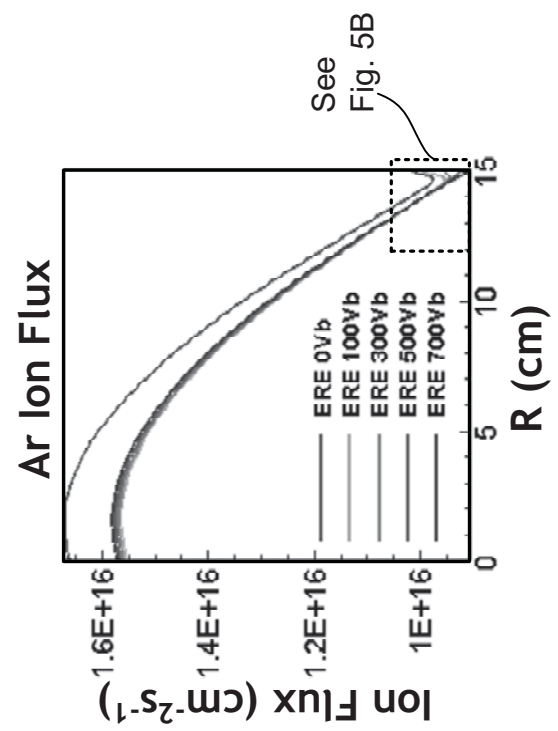


FIG . 5A

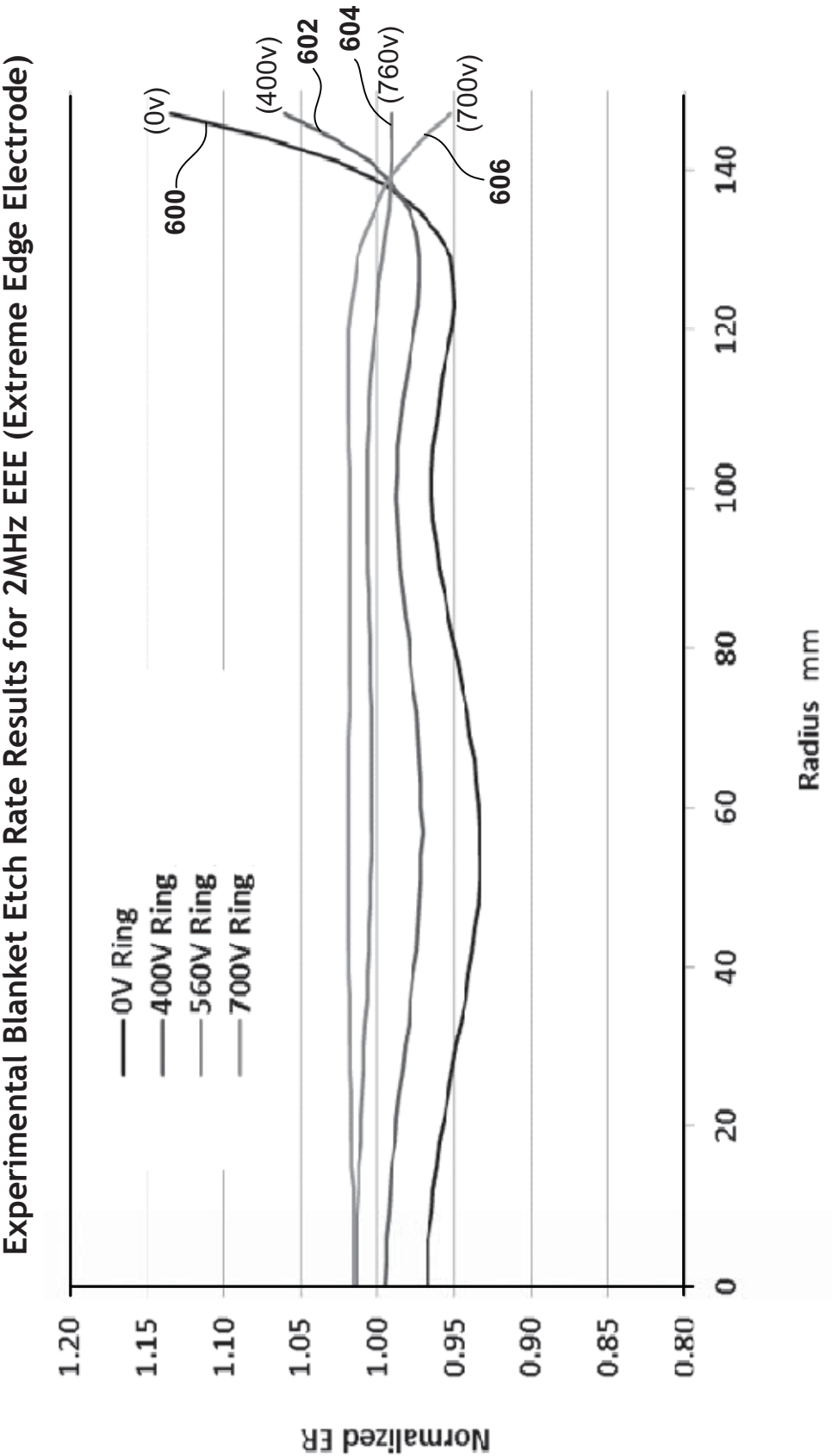
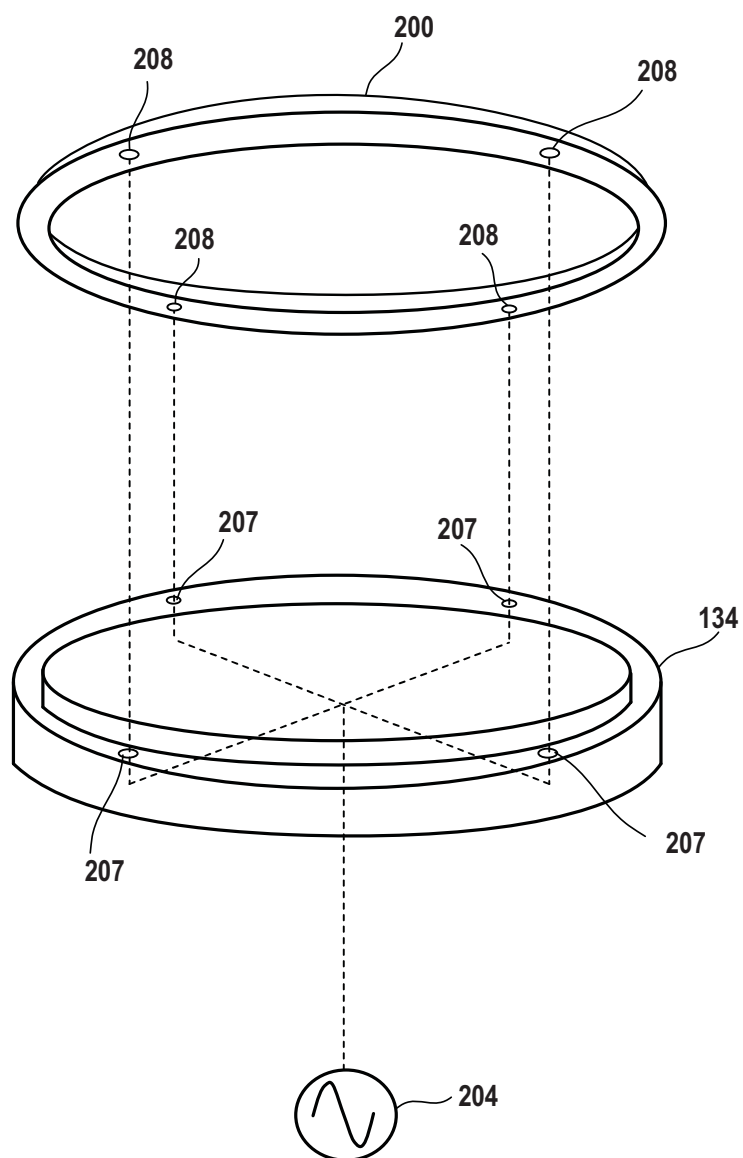


FIG. 6

**FIG. 7**

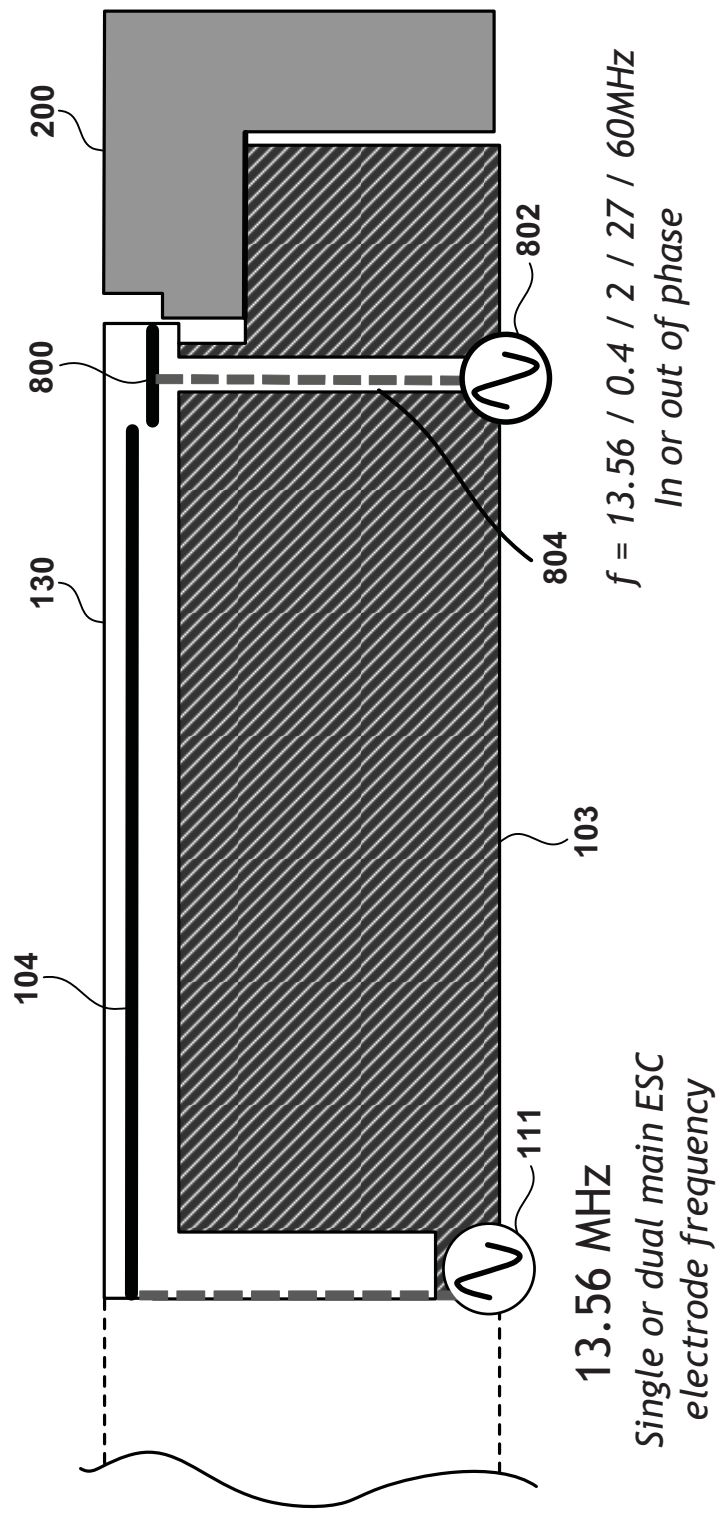
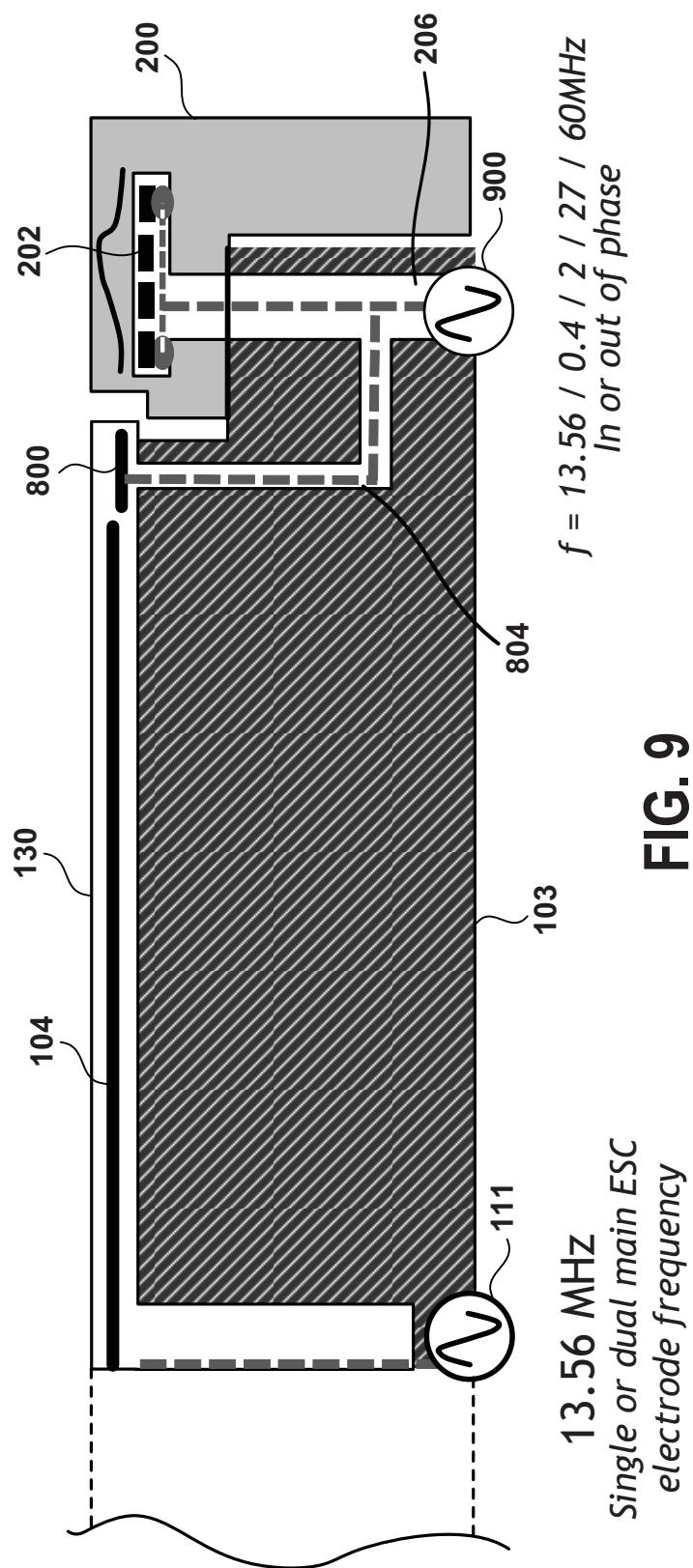


FIG. 8



10mT/900W TCP / 200Ar / 200V_{b,main} (10MHz) + 300Vb Bias on E (10 MHz), Phase X°

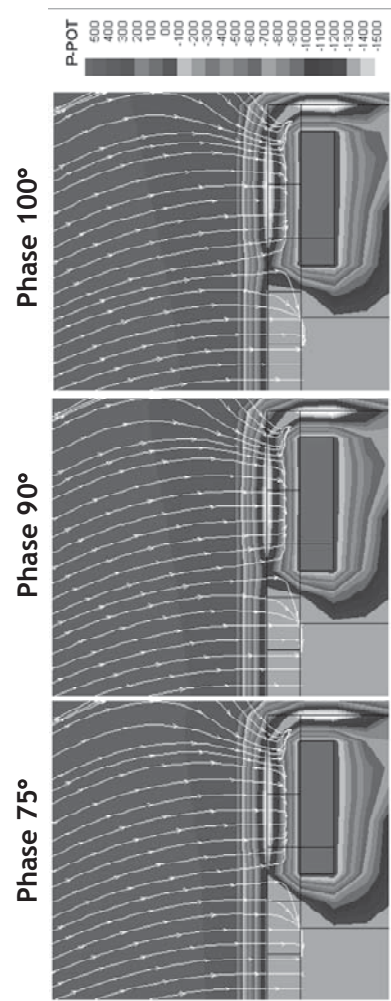
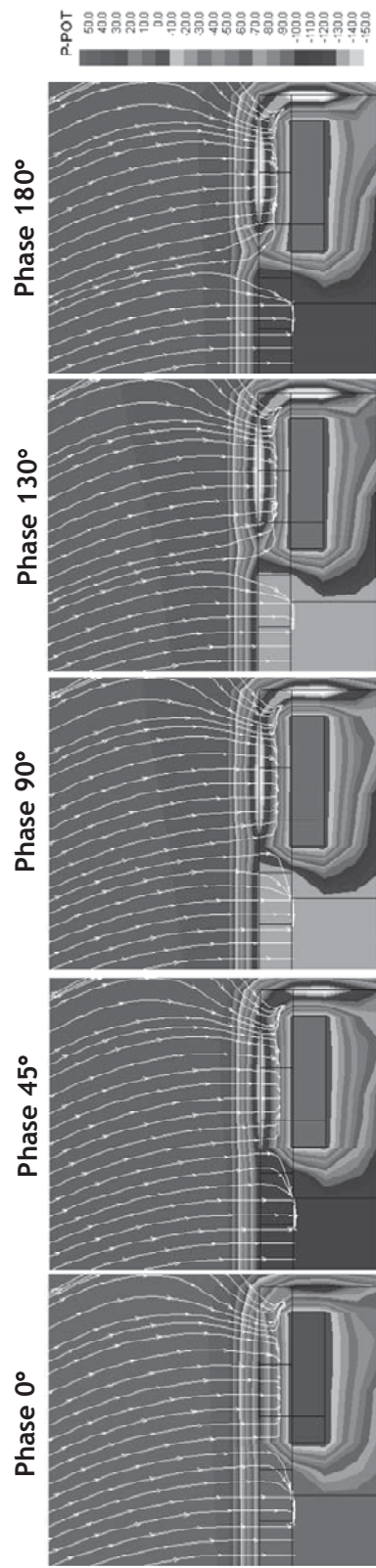


FIG. 10

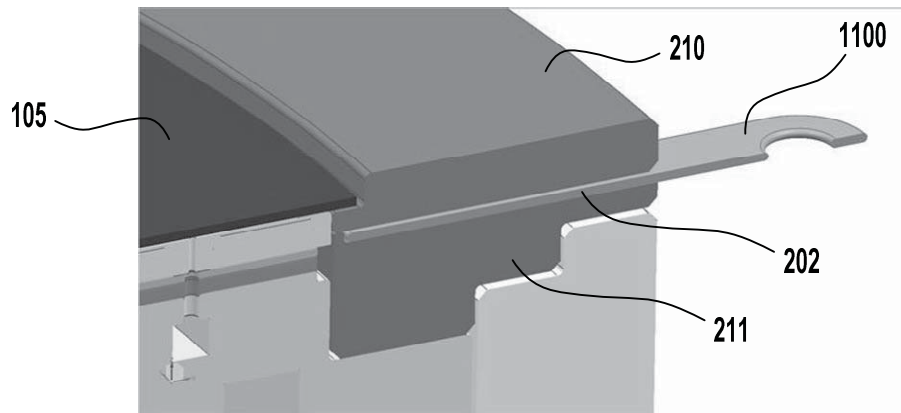


FIG. 11A

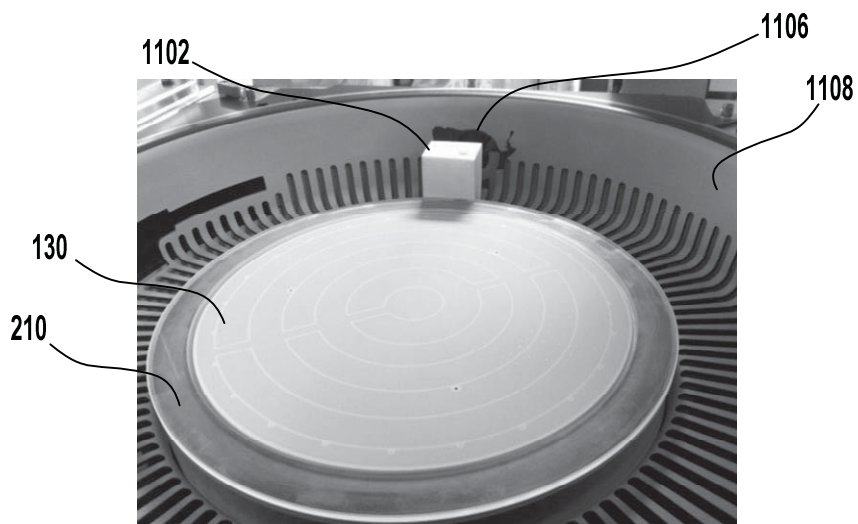


FIG. 11B

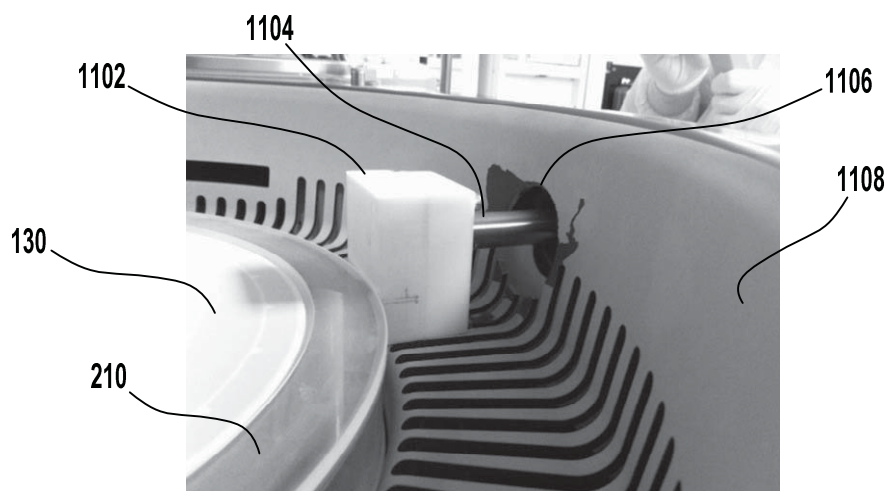


FIG. 11C

Nominal Baseline, Full Quartz Top Edge Ring

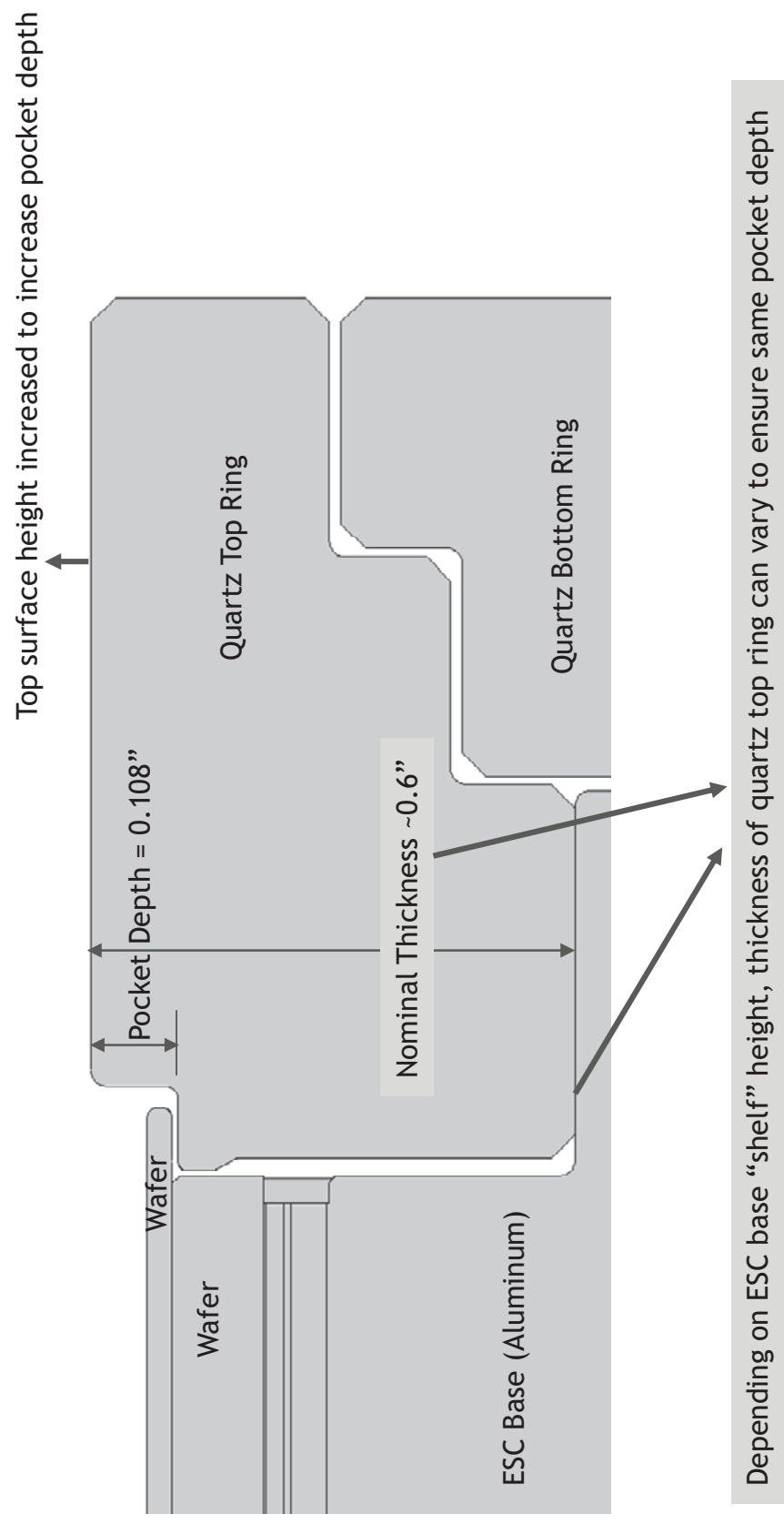


FIG. 12A

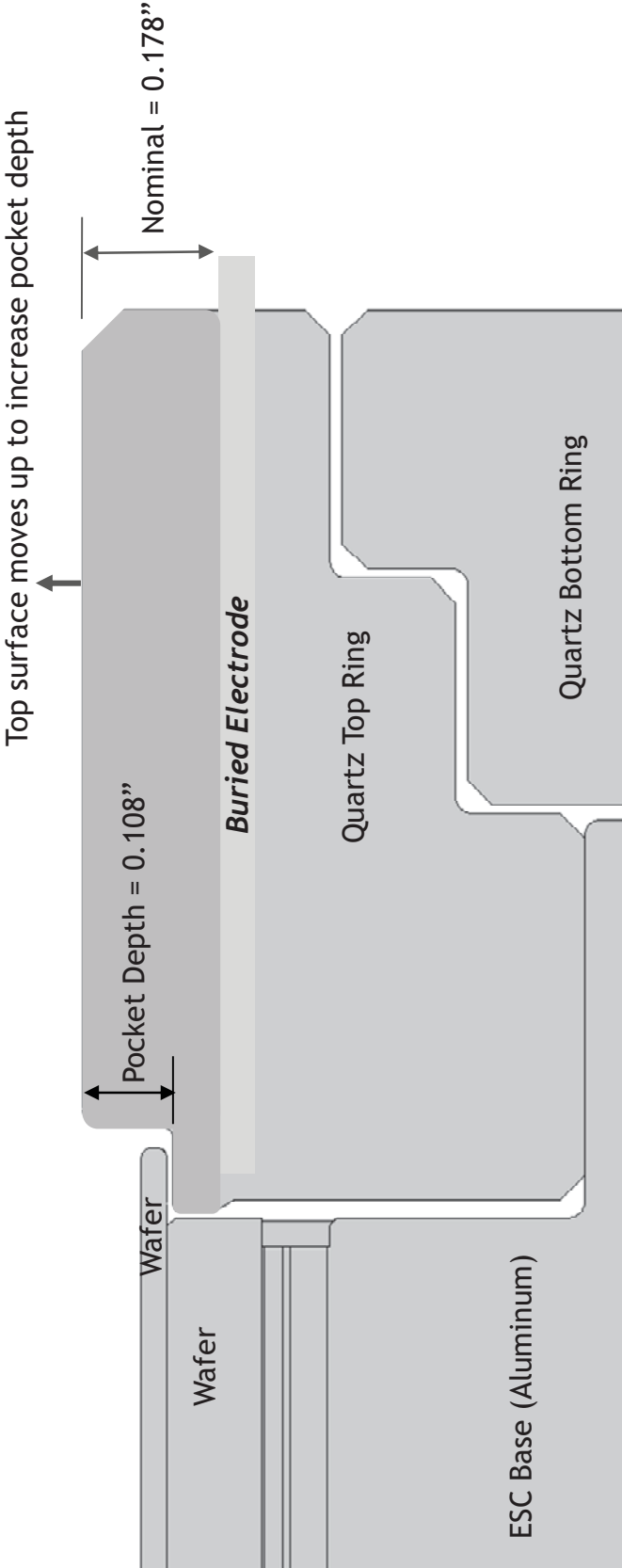


FIG. 12B

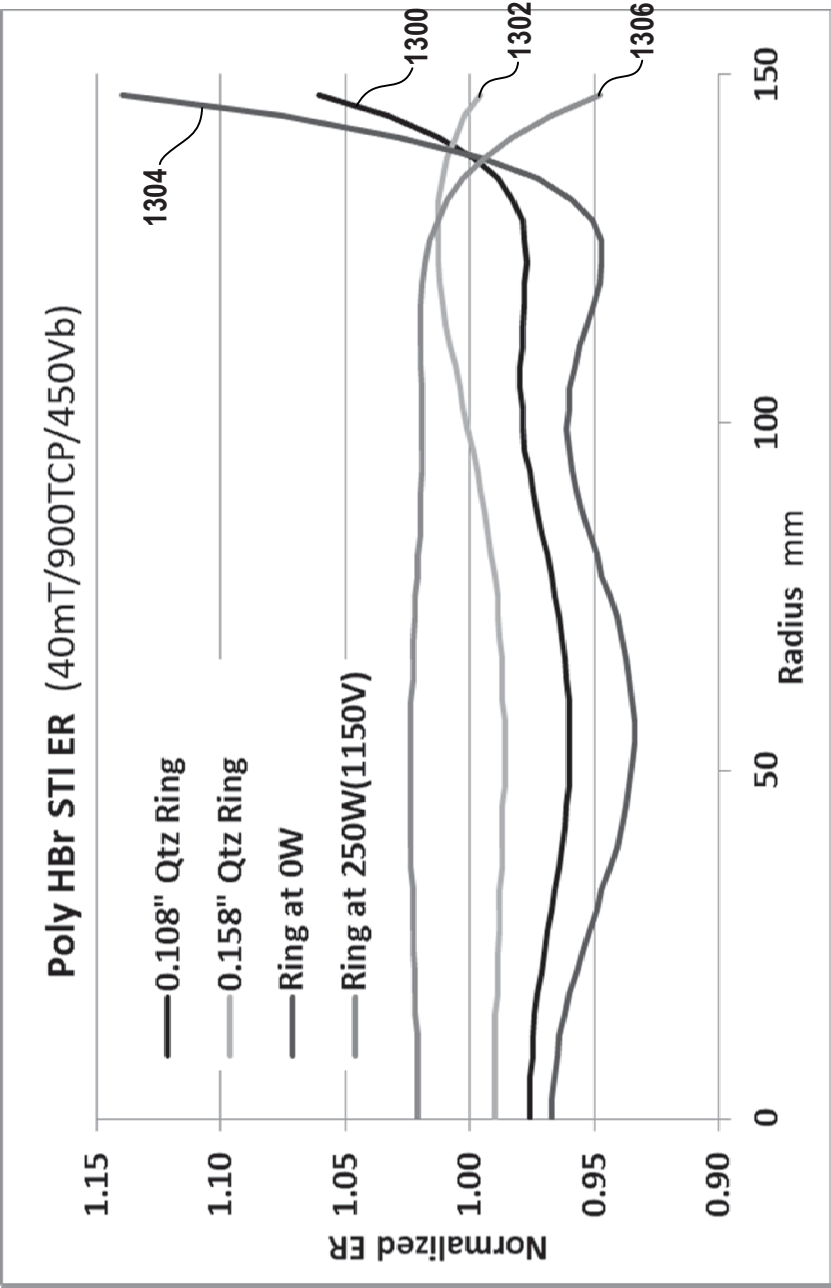
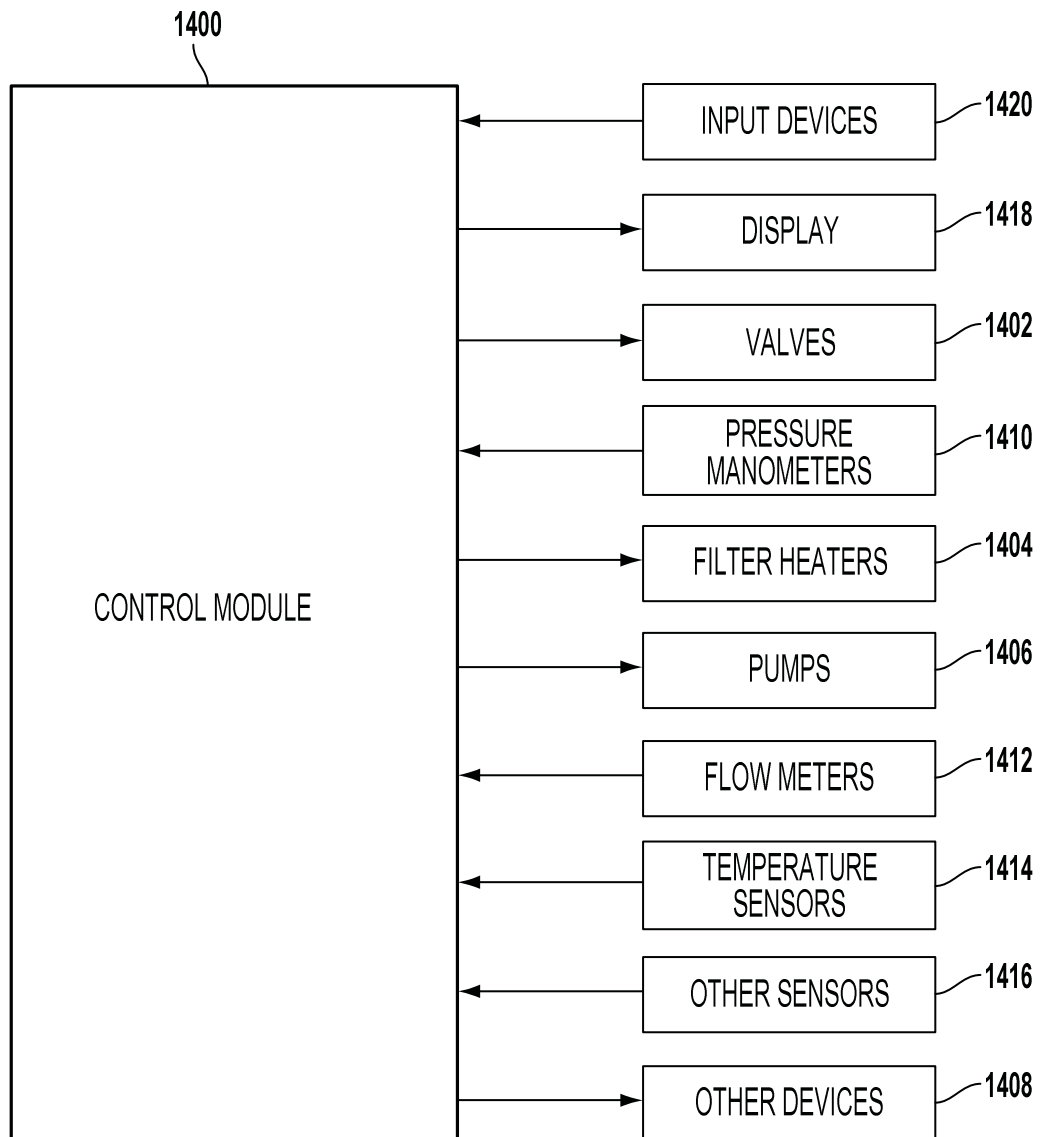


FIG. 13

**FIG. 14**